



TECH PUBLIC
台舟电子

IRFR3910

N-Channel 100-V (D-S) MOSFET

www.sot23.com.tw

Features

- $R_{DS(ON)} \leq 100\text{m}\Omega$ @ $V_{GS}=10\text{V}$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current

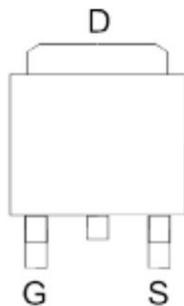
Application

- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

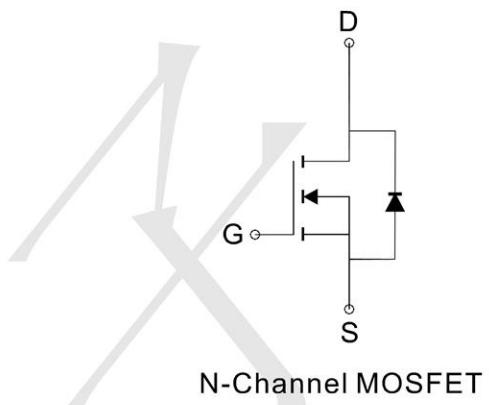
Package and Pin Configuration

(TO-252-3L)

Top View



Circuit diagram



Marking:



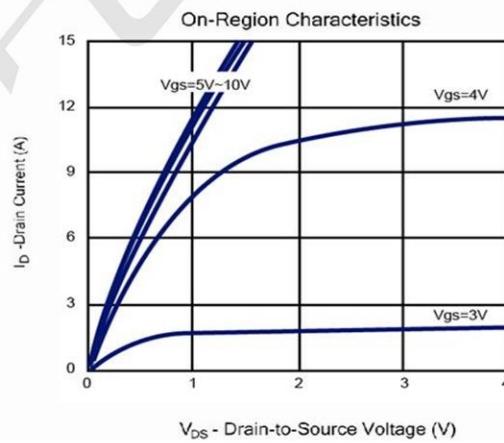
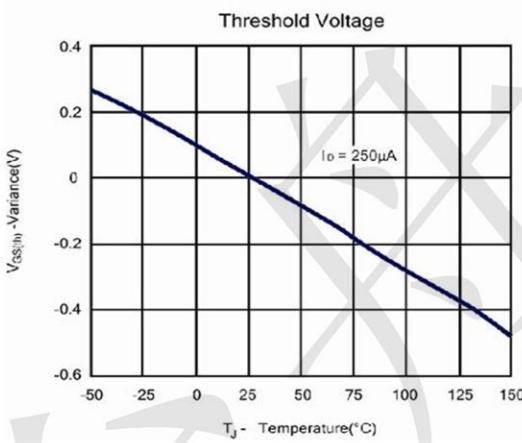
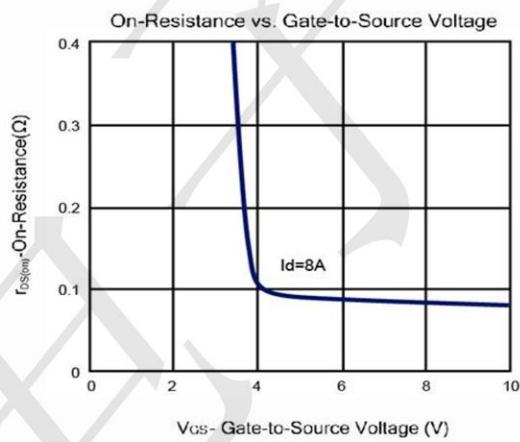
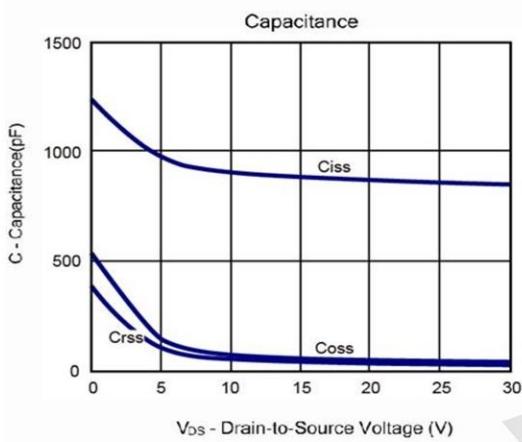
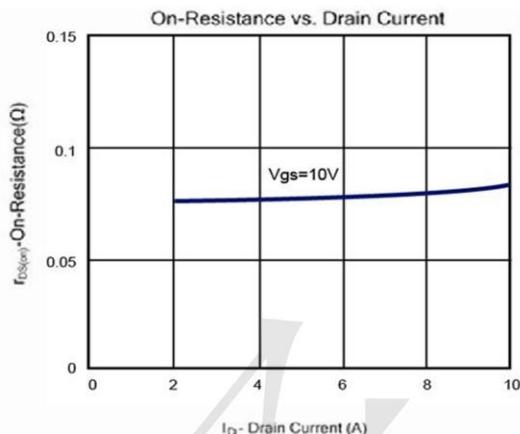
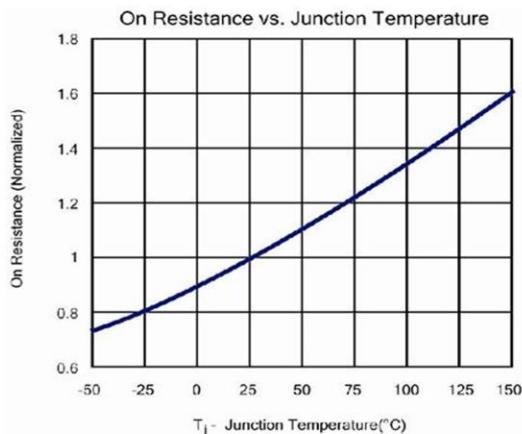
Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

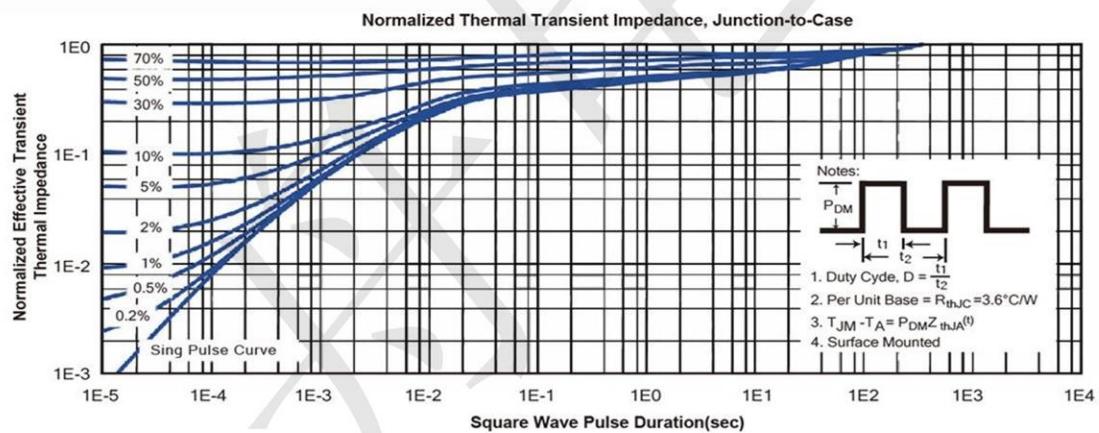
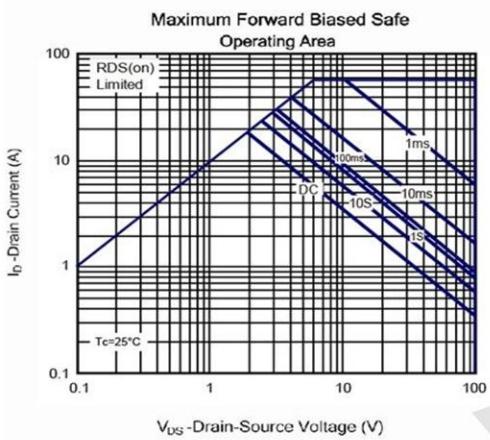
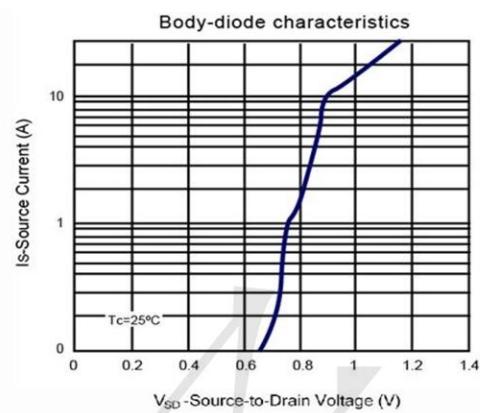
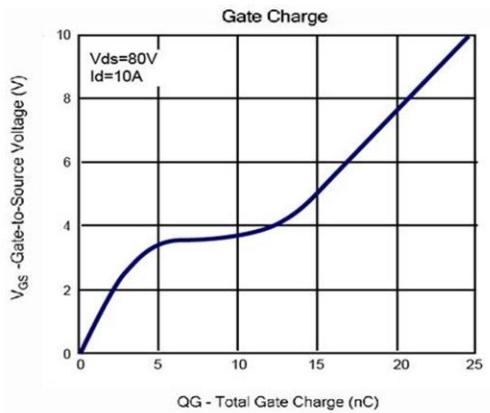
Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	14.7	A
		13.6	
Pulsed Drain Current	I_{DM}	59	A
Maximum Power Dissipation	P_D	34.7	W
		22.2	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	°C
Thermal Resistance-Junction to Case *	$R_{\theta JC}$	3.6	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

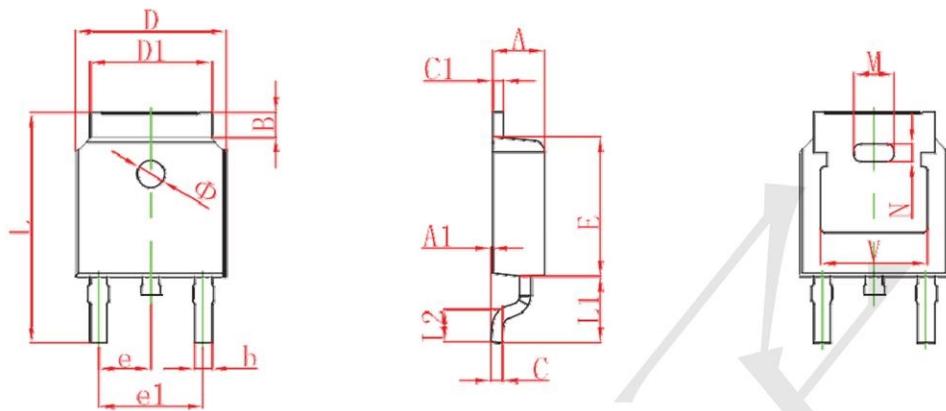
Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\ \mu\text{A}$	100			V
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\ \mu\text{A}$	1		3	V
I_{GSS}	Gate Leakage Current	$\text{V}_{\text{DS}}=0\text{V}, \text{V}_{\text{GS}}=\pm 20\text{V}$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$\text{V}_{\text{DS}}=80\text{V}, \text{V}_{\text{GS}}=0\text{V}$			1	μA
$\text{R}_{\text{DS(ON)}}$	Drain-Source On-Resistance ^a	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D= 8\text{A}$		80	100	$\text{m}\Omega$
V_{SD}	Diode Forward Voltage	$\text{I}_S=8\text{A}, \text{V}_{\text{GS}}=0\text{V}$		0.9	1.2	V
DYNAMIC						
Q_g	Total Gate Charge	$\text{V}_{\text{DS}}=80\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=10\text{A}$		24		nC
Q_g	Total Gate Charge			13		
Q_{gs}	Gate-Source Charge	$\text{V}_{\text{DS}}=80\text{V}, \text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=10\text{A}$		4.6		
Q_{gd}	Gate-Drain Charge			7.6		
C_{iss}	Input Capacitance			882		pF
C_{oss}	Output Capacitance	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1\text{MHz}$		57		
C_{rss}	Reverse Transfer Capacitance			44		
$\text{t}_{\text{d(on)}}$	Turn-On Delay Time			14		ns
t_r	Turn-On Rise Time	$\text{V}_{\text{DS}}=50\text{V}, \text{R}_L = 5\Omega,$ $\text{V}_{\text{GS}}=10\text{V}, \text{R}_G=1\Omega$		33		
$\text{t}_{\text{d(off)}}$	Turn-Off Delay Time			39		
t_f	Turn-Off Fall Time	$\text{I}_D=1\text{A}$		5		

Typical Electrical and Thermal Characteristic Curves





TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Y	1.100	1.300	0.043	0.0±1